HG Semiconductors

HG RF POWER TRANSISTOR

RF1076AMP

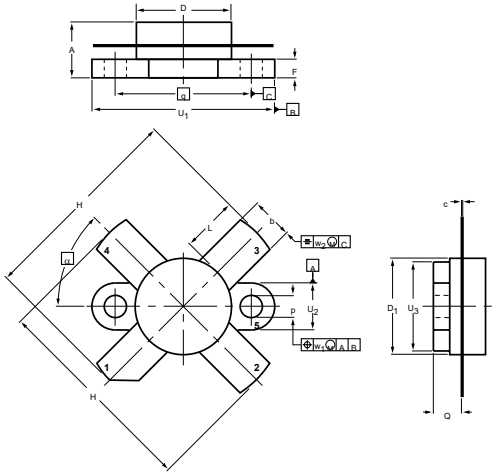
ROHS Compliance,Silicon NPN POWER TRANSISTOR

DESCRIPTION

Designed primarily for applications as high-power linear power amplifier from 2.0 to 30MHz

FEATURES

- Output Power: 220W(Min)
- Power Gain: 12 dB Min@30M, 28V
- Efficiency: 40% Min@30M, 28V
- Intermodulation Distortion: -30dBc Max@30M, 28V



1.Collector
2.EMITTER
3.BASE
4.EMITTER
5.FIN

DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANCE.

UNIT	A	b	c	D	D_1	F	H	L	p	Q	q	U_1	U_2	U_3	w_1	w_2	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CBO}	70	V
Collector-Emitter Voltage	V_{CES}	70	V
Collector-Emitter Voltage	V_{CEO}	35	V
Collector Current	I_C	16	A
Emitter-Base Voltage	V_{EBO}	4	V
Collector Power Dissipation	P_{DISS}	320	W
Junction Temperature	T_J	200	°C
Storage Temperature Range	T_{STG}	-65 to 150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=200mA,I_B=0	35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=100mA,V_{EB}=0	70	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=20mA,I_C=0	4	-	-	V
Collector Cutoff Current	I_{CEO}	V_{CE}=30V,I_E=0	-	-	5	mA
DC Current Gain	h_{FE}	V_{CE}=5V,I_C=7A	10	-	120	-
Collector Output Capacitance	C_{Ob}	V_{CB}=28V,I_E=0 f=1MHz	-	460	-	pF
Power Gain	G_P	V_{CC}=28V,P_{OUT}=220	12.0	-	-	dB
Collector Efficiency	η_C	W, f=28M,	40	-	-	%
Intermodulation Distortion	IMD	28.001MHz	-	-	-30	dBc

Note : Above parameters , ratings , limits and conditions are subject to change.